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UNIVERSITY OF CALIFORNIA
Department of Electrical Engineering and Computer Sciences
EE 130 Fall 2003

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Test #1

1) Consider the following elements:

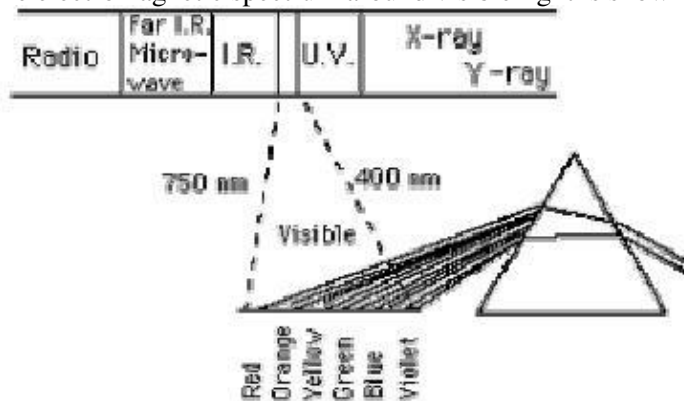
Zn: Atomic number: 30, Atomic weight: 65

O: Atomic number: 8, Atomic weight: 16

a) Write the electronic configurations (1s², 2s², ...) for both elements (2pts)

b) Two Zinc Oxides are known to exist. ZnO and ZnO₂. Which material is likely to be a semiconductor? Why? (1 pt)

c) The portion of the electromagnetic spectrum around visible light is shown below.



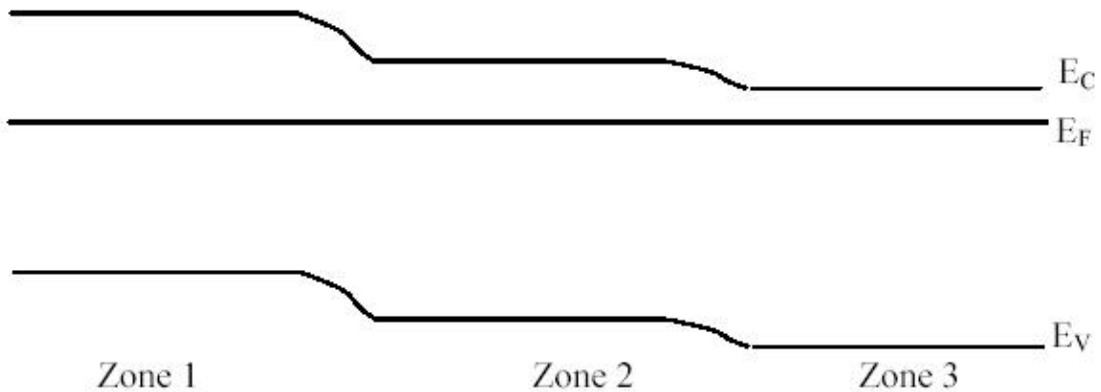
Frequencies: 4 - 7.5 x 10¹⁴ Hz

Wavelengths: 750 - 400 nm

Quantum energies: 1.65 - 3.1 eV

The Zinc Oxide semiconductor from above is known to be almost entirely transparent to visible light, yet, also forms a decent semiconductor at room temperature. Suggest a likely bandgap for the material. Give reasons for your answer. (2 pts)

2) Consider a block of silicon that is doped into three zones, each 1cm long with phosphorus concentrations of $1E16$, $1E17$, and $1E18$ cm⁻³ respectively.



a) Based on the band diagram above, determine which doping level corresponds to each zone (1.5 pts)

i) Zone 1:

ii) Zone 2:

iii) Zone 3:

b) What is the voltage applied across the piece of silicon above? Give reasons. (1 pt)

c) Estimate the resistances of the three zones, assuming the cross-sectional area is $1\text{cm} \times 1\text{cm}$. Ignore the curved regions on the band diagram above: (1.5 pts)

i) Zone 1:

ii) Zone 2:

iii) Zone 3:

d) Suppose I apply 0.6V across the block, with the anode connected on the left. Sketch the resulting band diagram, indicating the approximate voltage drop across each region. (4 pts)

3) Suppose I take a block of silicon and dope it with $1E17\text{cm}^{-3}$ Arsenic.

a) What is the concentration of electrons and holes at room temperature? (1 pt)

b) Now, suppose I add $1E18\text{cm}^{-3}$ Indium to this block. Will the resulting material be Ntype, intrinsic, or P-type. Give reasons. (2 pts)

c) Which dopant will be more completely ionized. Why? (2 pts)

d) Now, suppose I add an additional $1E19\text{cm}^{-3}$ of Indium. Will the %ionization of Indium Increase or decrease. Sketch a plot of the Fermi function in the two cases to illustrate your answer. (3 pts)

e) Suppose I were to have used Boron instead of Indium in parts (b) and (d) above. Would the resistance of the block increase, decrease, or stay the same. Give reasons for your answer. (2 pts)

f) Compare the hole mobility of two identical blocks of silicon at room temperature. Block "A" is moderately doped ($\sim 1E17$ or so) with Boron, while Block "B" is doped with an identical amount of Indium. Give reasons for your answer. (2 pts)